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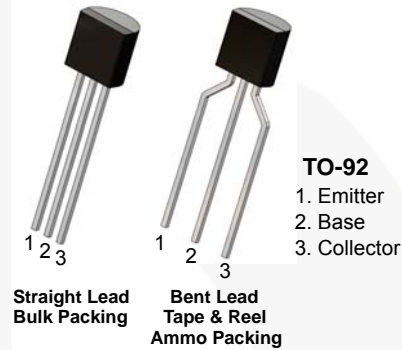


September 2015

# KSP44 / KSP45 NPN Epitaxial Silicon Transistor

## Features

- High-Voltage Transistor
- Collector-Emitter Voltage:  $V_{CEO}$  = KSP44: 400 V  
KSP45: 350 V



## Ordering Information

Part Number	Top Mark	Package	Packing Method
KSP44BU	KSP44	TO-92 3L	Bulk
KSP44TA	KSP44	TO-92 3L	Ammo
KSP44TF	KSP44	TO-92 3L	Tape and Reel
KSP45TA	KSP45	TO-92 3L	Ammo

## Absolute Maximum Ratings

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Value	Unit
$V_{CBO}$	Collector-Base Voltage	KSP44	500
		KSP45	400
$V_{CEO}$	Collector-Emitter Voltage	KSP44	400
		KSP45	350
$V_{EBO}$	Emitter-Base Voltage	6	V
$I_C$	Collector Current	300	mA
$T_J$	Junction Temperature	150	$^\circ\text{C}$
$T_{STG}$	Storage Temperature	-55 to 150	$^\circ\text{C}$

KSP44 / KSP45 — NPN Epitaxial Silicon Transistor

## Thermal Characteristics<sup>(1)</sup>

Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Value	Unit	
$P_D$	Power Dissipation	$T_A = 25^\circ\text{C}$	625	mW
		$T_C = 25^\circ\text{C}$	1.5	W
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	83.3	$^\circ\text{C/W}$	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	200	$^\circ\text{C/W}$	

### Note:

1. PCB size: FR-4, 76 mm x 114 mm x 1.57 mm (3.0 inch x 4.5 inch x 0.062 inch) with minimum land pattern size.

## Electrical Characteristics

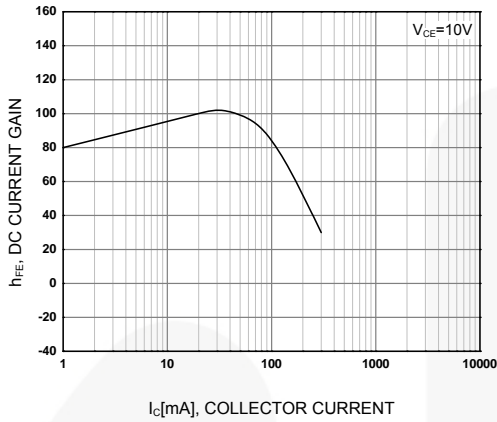
Values are at  $T_A = 25^\circ\text{C}$  unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Max.	Unit	
$BV_{CBO}$	Collector-Base Breakdown Voltage	KSP44	$I_C = 100\ \mu\text{A}, I_E = 0$	500		V
		KSP45		400		
$BV_{CEO}$	Collector-Emitter Breakdown Voltage <sup>(2)</sup>	KSP44	$I_C = 1\ \text{mA}, I_B = 0$	400		V
		KSP45		350		
$BV_{EBO}$	Emitter-Base Breakdown Voltage	$I_E = 100\ \mu\text{A}, I_C = 0$	6		V	
$I_{CBO}$	Collector Cut-Off Current	KSP44	$V_{CB} = 400\ \text{V}, I_E = 0$		0.1	$\mu\text{A}$
		KSP45		$V_{CB} = 320\ \text{V}, I_E = 0$		
$I_{CES}$	Collector Cut-Off Current	KSP44	$V_{CE} = 400\ \text{V}, I_B = 0$		0.5	$\mu\text{A}$
		KSP45		$V_{CE} = 320\ \text{V}, I_B = 0$		
$I_{EBO}$	Emitter Cut-Off Current	$V_{EB} = 4\ \text{V}, I_C = 0$		0.1	$\mu\text{A}$	
$h_{FE}$	DC Current Gain <sup>(2)</sup>		$V_{CE} = 10\ \text{V}, I_C = 1\ \text{mA}$	40		
			$V_{CE} = 10\ \text{V}, I_C = 10\ \text{mA}$	50	200	
			$V_{CE} = 10\ \text{V}, I_C = 50\ \text{mA}$	45		
			$V_{CE} = 10\ \text{V}, I_C = 100\ \text{mA}$	40		
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage <sup>(2)</sup>		$I_C = 1\ \text{mA}, I_B = 0.1\ \text{mA}$		0.40	V
			$I_C = 10\ \text{mA}, I_B = 1\ \text{mA}$		0.50	
			$I_C = 50\ \text{mA}, I_B = 5\ \text{mA}$		0.75	
$V_{BE(sat)}$	Base-Emitter Saturation Voltage <sup>(2)</sup>	$I_C = 10\ \text{mA}, I_B = 1\ \text{mA}$		0.75	V	
$C_{ob}$	Output Capacitance	$V_{CB} = 20\ \text{V}, I_E = 0,$ $f = 1\ \text{MHz}$		7	pF	

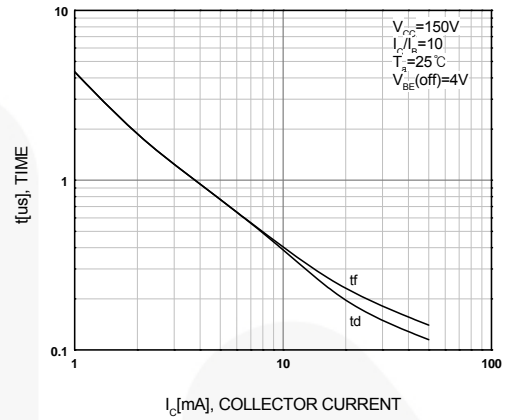
### Note:

2. Pulse test: pulse width  $\leq 300\ \mu\text{s}$ , duty cycle  $\leq 2\%$ .

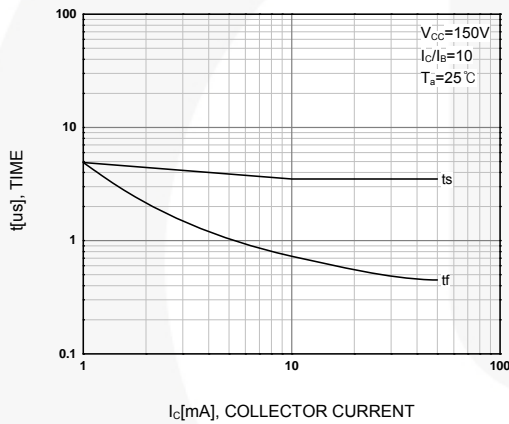
## Typical Performance Characteristics



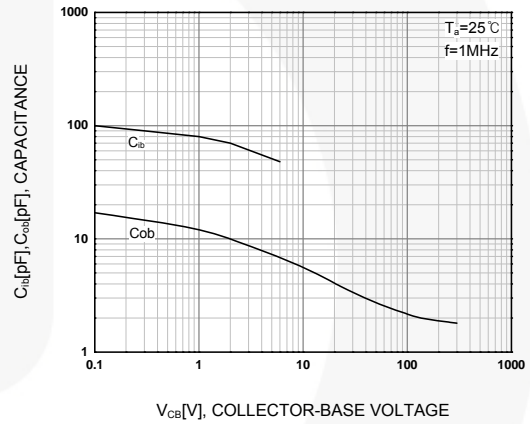
**Figure 1. DC Current Gain**



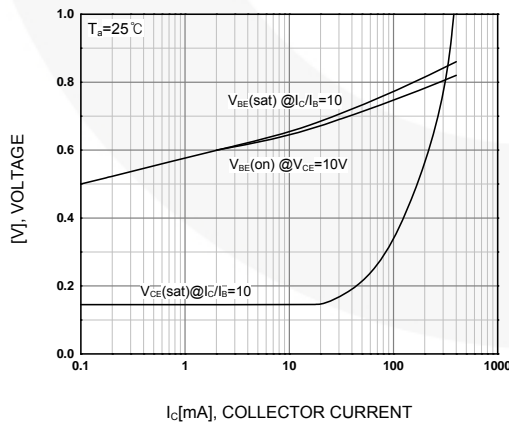
**Figure 2. Turn-On Switching Times**



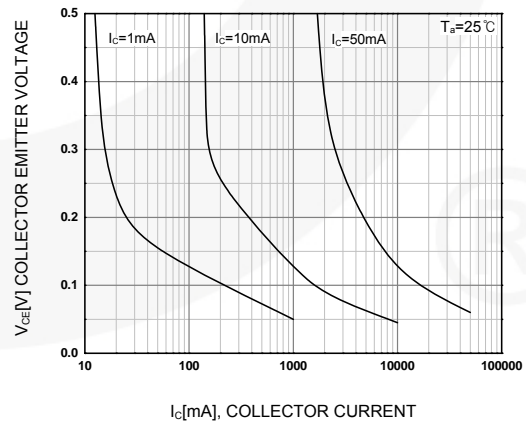
**Figure 3. Turn-Off Switching Times**



**Figure 4. Capacitance**



**Figure 5. On Voltage**



**Figure 6. Collector Saturation Region**

Typical Performance Characteristics (Continued)

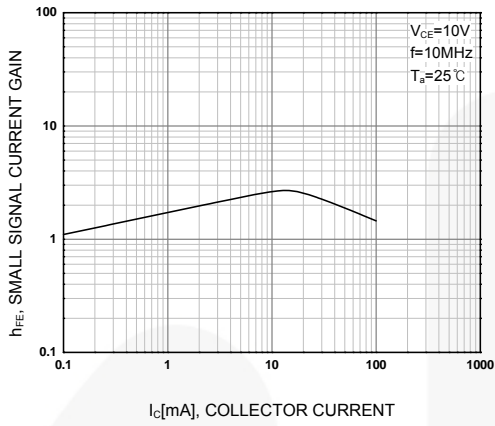


Figure 7. High-Frequency Current Gain

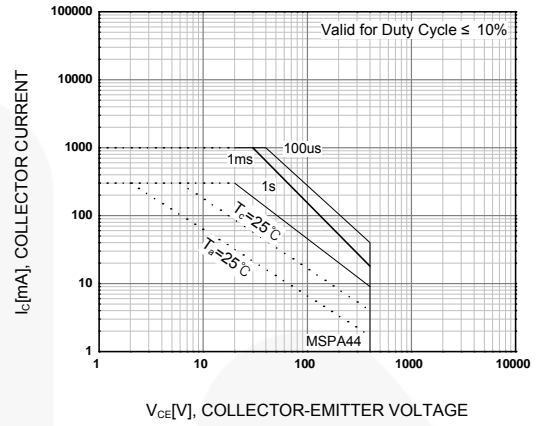
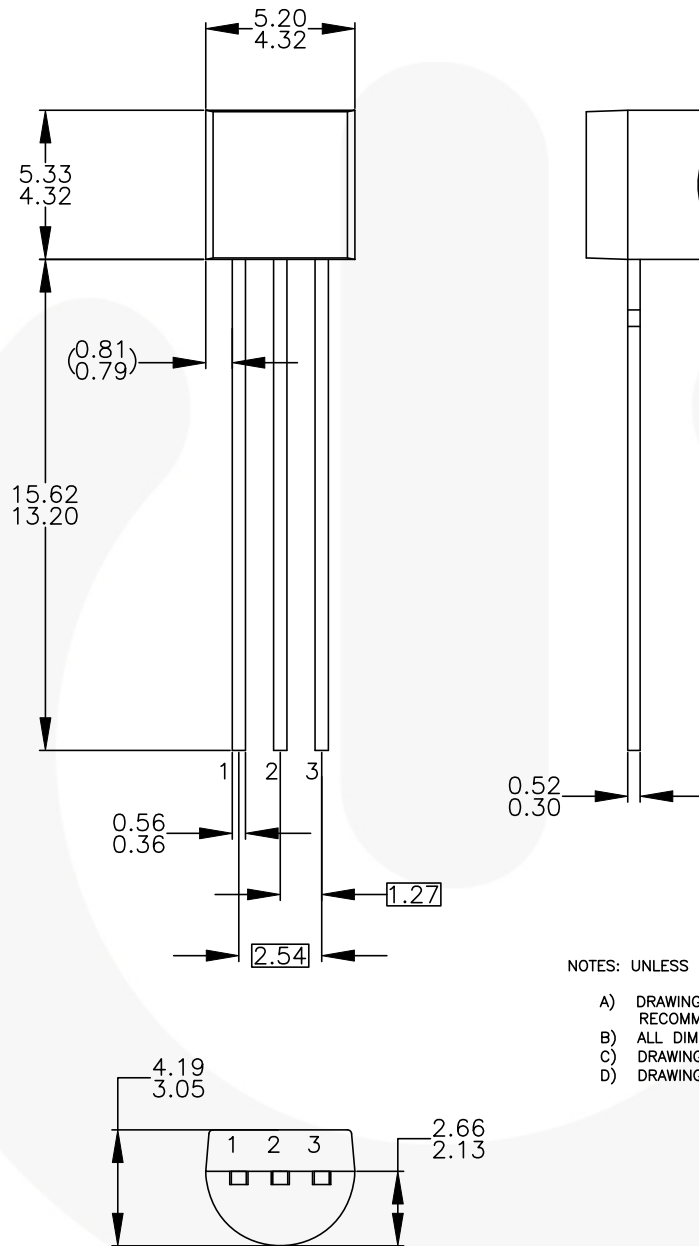


Figure 8. Safe Operating Area

Physical Dimensions



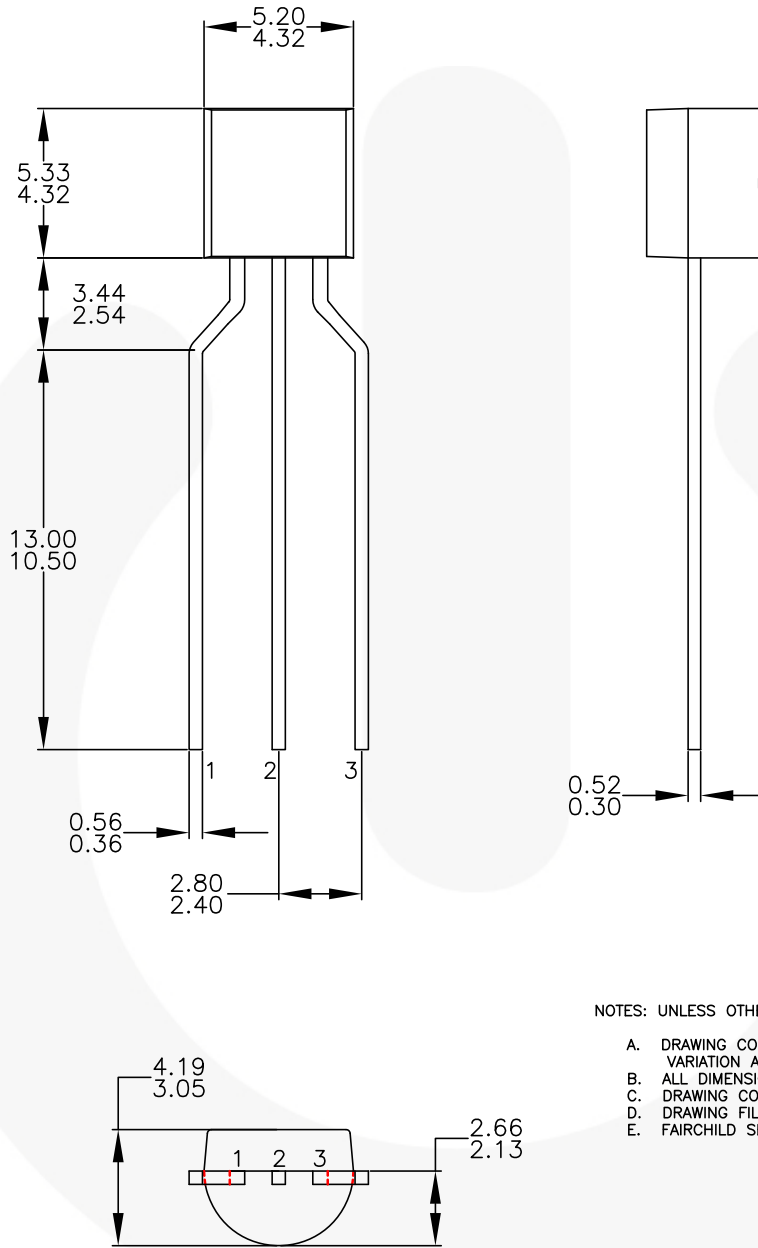
NOTES: UNLESS OTHERWISE SPECIFIED

- A) DRAWING WITH REFERENCE TO JEDEC TO-92 RECOMMENDATIONS.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DRAWING CONFORMS TO ASME Y14.5M-2009.
- D) DRAWING FILENAME: MKT-ZA03DREV4.



Figure 9. 3-Lead, TO-92, JEDEC TO-92 Compliant Straight Lead Configuration, Bulk Type

Physical Dimensions (Continued)



NOTES: UNLESS OTHERWISE SPECIFIED

- A. DRAWING CONFORMS TO JEDEC MS-013, VARIATION AC.
- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DRAWING CONFORMS TO ASME Y14.5M-2009.
- D. DRAWING FILENAME: MKT-ZA03FREV3.
- E. FAIRCHILD SEMICONDUCTOR.

Figure 10. 3-Lead, TO-92, Molded, 0.2 In Line Spacing Lead Form, Ammo, Tape and Reel Type